

IN THE CLAIMS:

Claims 1-8 and 10-12 are pending in this application.

1. (Previously Presented) An image display device having an active matrix substrate provided with a pixel region having a plurality of pixels arranged in a matrix configuration, and a drive circuit region disposed outside of said pixel region for supplying drive signals to said plurality of pixels via interconnection lines,
wherein said drive circuit region comprises a plurality of stages of circuit sections successively processing an externally supplied display signal to produce a drive signal to be supplied to said pixel region, each of said plurality of stages of circuit sections having a different function, and said plurality of stages of circuit sections includes a shift register, a digital-analog converter, a buffer circuit, and a sampling circuit,
wherein active elements in each of said shift register, said digital-analog converter, and said buffer circuit use roughly-band-shaped-crystal silicon films having grain boundaries as channels of said active elements, each of the grain boundaries of the roughly-band-shaped-crystal silicon films being continuous in generally one direction, and
said active elements in said shift register, said digital-analog converter, and said buffer circuit have a direction of movement of carriers therein in a direction of said grain boundaries, and
wherein active elements in said sampling circuit use granular polysilicon films having loop-like grain boundaries as channels of said active elements.
2. (Original) An image display device according to claim 1, wherein said circuit sections of each of said plurality of stages are arranged along one side of said active matrix substrate at specified intervals at a periphery thereof.
3. (Original) An image display device according to claim 1, wherein circuit sections having said active elements formed therein are in a final output stage of said plurality of stages, and

said interconnection lines coupling said final output stage to said plurality of pixels are arranged at wider intervals on a pixel-region side thereof than on a final-output-stage side thereof.

4. (Original) An image display device according to claim 1, wherein said circuit sections having said active elements formed therein are arranged in two or more parallel rows along one side of said active matrix substrate at specified intervals at a periphery thereof.
5. (Original) An image display device according to claim 1, wherein said active elements are arranged along two opposed sides of said active matrix substrate at specified intervals at peripheries thereof.
6. (Original) An image display device according to claim 1, wherein areas of said circuit sections having said active elements formed therein vary with a scale thereof.
7. (Original) An image display device according to claim 1, wherein said circuit sections having said active elements formed therein are arranged in two or more parallel rows along one side of said active matrix substrate, and said circuit sections in one of said two or more rows are offset in longitudinal directions thereof from said circuit sections in an adjacent one of said two or more rows.
8. (Previously Presented) An image display device according to claim 1, wherein said active elements are arranged in two or more parallel rows along one side of said active matrix substrate, and said active elements in one of said two or more parallel rows are offset in longitudinal directions thereof from said active elements in an adjacent one of said two or more parallel rows.
9. (Canceled)
10. (Original) An image display device according to claim 1, further comprising a color filter substrate and a liquid crystal layer, wherein said liquid crystal layer is

sandwiched between said active matrix substrate and said color filter substrate superposed on said active matrix substrate with a specified spacing therebetween.

11. (Original) An image display device according to claim 1, wherein each of said pixels further comprises an organic EL layer.
12. (Previously Presented) An image display device according to claim 1, wherein said active elements are thin film transistor.